<u>Linear Voltage Regulator</u> -Dual, V_{in} and V_{out} Voltage Detector

The NCP4672 is a dual linear voltage regulator with input voltage and output voltage detectors. This part is useful in systems where multiple voltages are required such as for core and I/O. The NCP4672 is very accurate at 2% over full input voltage and full load current. The NCP4672 eliminates the need for external voltage supervision due to the two built in voltage detectors. The voltage detector on the input is set to 7.0 V. The output voltage detector is for channel 1 and is set to 2.9 V. An external capacitor is used to set the duration of this reset signal. Other features include short circuit protection and thermal shutdown protection. The NCP4672 has been designed to work with a 4.7 μ F output capacitor having an ESR between 0.1 Ω and 5.0 Ω .

Features

- Accuracy: 2% at Full Voltage and Load
- Excellent Ripple Rejection: 70 dB @ 1 kHz
- Voltage Detector for Input Voltage
- Voltage Detector for Output Voltage
- Programmable Delay of Reset Signal
- Thermal Short Circuit Protection
- This is a Pb-Free Device

Typical Application

- Small Core and I/O Power
- Consumer Equipment
- Measurement Equipment
- Industrial Equipment

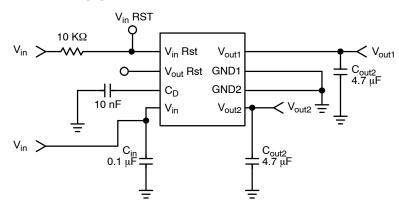


Figure 1. Typical Application Circuit



ON Semiconductor®

http://onsemi.com

MARKING DIAGRAM



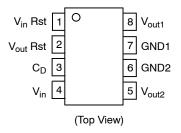
SOIC-8 NB SUFFIX CASE 751



4672 = Specific Device Code A = Assembly Location

L = Wafer Lot Y = Year W = Work Week ■ = Pb-Free Package

PIN CONFIGURATION



ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-------------|---------------------|-----------------------|
| NCP4672DR2G | SOIC-8 (Pb-Free) | 2500 Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|--|--|------------------|
| Input Voltage | V _{inmax} | − 0.3 ~ 18 | V |
| Output Voltage | V _{out} | -0.3 to V _{in} + 0.3 | V |
| Output Current 1 Output Current 2 | l _{out1max} l _{out2max} | 30 80 | mA mA |
| Output Short Circuit Duration | - | Infinite | - |
| Power Dissipation and Thermal Characteristics – SOIC–8 Power Dissipation Thermal Resistance, Junction–to–Ambient Minimum Pad Size 200 mm² Pad Size (Note 1) Thermal Resistance, Junction–to–Case | P _D R _{θJA} R _{θJC} | Internally Limited 190 160 25 | W °C/W °C/W °C/W |
| Operating Junction Temperature Range | T _{stg} | -40 to 125 | °C |
| Storage Temperature Range | T _{solder} | -55 to 150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

PIN DESCRIPTION

| Pin Number | Symbol | Description |
|---------------|---------------------|---|
| 1 | V _{in RST} | Open–collector, active–low output of the input voltage detector with hysteresis. Threshold levels are typical 7.0 V/ 7.35 V at $V_{\rm CC}$ pin. |
| 2 | V _{o RST} | Active–low output of the reset generator. Reset generator is based on sensing of the V_{out1} voltage. Sensing is with hysteresis – threshold levels are typically 2.9 V/ 2.95 V at V_{out1} . Reset is generated at rising edge of the V_{out1} and it's duration is set by external capacitor connected to C_D pin. |
| 3 | C _D | Programmable delay of the reset generator. Delay is adjusted by inserting a capacitor between C_D and GND (typically 10 ms for 10 nF capacitor). |
| 4 | V _{CC} | Supply Voltage |
| 5 | V _{out2} | 1.8 V/ 80 mA LDO Regulator Output |
| 6 | GND2 | Ground for V _{out2} (internally connected with GND1) |
| 7 | GND1 | Ground for V _{out1} (internally connected with GND2) |
| 8 | V _{out1} | 3.5 V/30 mA LDO Regulator Output |

RECOMMENDED CONDITIONS (T_A = 25°C, C_{in} = 0.1 μF Ceramic, C_{out} = 4.7 μF)

| Characteristics | Symbol | Min | Тур | Max | Unit |
|---|--|--------|--------|----------|------|
| Input Voltage | V _{in} | 3.8 | 12 | 16 | V |
| Output Current (where V _{out} remains within accuracy) | I _{out1} I _{out2} | 0 0 | - - | 20 70 | mA |

^{1.} Refer to Figure 4 for more information.

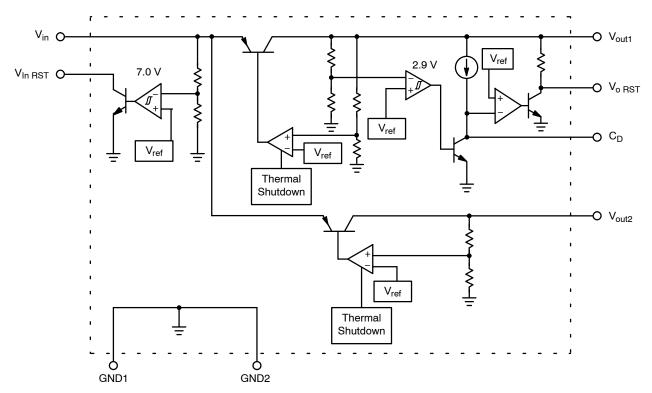


Figure 1.

ELECTRICAL CHARACTERISTICS (C_{in} = 0.1 μF Ceramic, C_{out} = 4.7 μF with ESR = 0.1 – 5.0 Ω , V_{in} = 12 V, T_A = 25°C)

| Characteristics | Symbol | Min | Тур | Max | Unit |
|---|--|-------------------|------------|---------------|---------------|
| Output Voltage V_{out1} (V_{in} = 4.5 V, I_{out1} = 20 mA) V_{out2} (V_{in} = 4.5 V, I_{out2} = 40 mA) | V_{adj} | 3.43 1.764 | 3.5 1.8 | 3.57 1.836 | V |
| Line Regulation V_{out1} (V_{in} = 4.5 V , I_{out1} = 20 mA) V_{out2} (V_{in} = 4.5 V to 10 V, I_{out2} = 40 mA) | Reg _{line} | - - | 3.0 3.0 | 30 30 | mV |
| Load Regulation $ \begin{array}{l} V_{out1} \ (V_{in} = 4.5 \ V, \ I_{out1} = 0.1 \ mA \ to \ 20 \ mA) \\ V_{out2} \ (V_{in} = 4.5 \ V, \ I_{out2} = 0.1 \ mA \ to \ 70 \ mA) \end{array} $ | Reg _{load} | - - | 3.0 2.0 | 40 40 | mV |
| Dropout Voltage V _{out1} (V _{in} = 3.3 V, I _{out1} = 20 mA) | V _{in} – V _{out1} | - | 150 | 300 | mV |
| Ground Pin Current | I _{GND} | - - | 1.0 3.0 | 2.0 - | mA |
| Short Current Limit Vout1 Vout2 | I _{SC} | 30 80 | 60 150 | - - | mA |
| Thermal Shutdown | | - | 165 | - | °C |
| Temperature Coefficient V_{out1} (T_J = -30 to 85°C, V_{in} = 4.5 V, I_{out1} = 20 mA) V_{out2} (T_J = -30 to 85°C, V_{in} = 4.5 V, I_{out2} = 40 mA) | T _C | | 100 100 | - - | ppm/°C |
| Ripple Rejection (Note 6) V _{out1} (V _{in} = 4.5 V, V _{ripple} = 1.0 V, I _{out1} = 20 mA, 120 Hz) V _{out2} (V _{in} = 4.5 V, V _{ripple} = 1.0 V, I _{out2} = 40 mA, 120 Hz) | R _R | - - | 65 70 | - - | dB |
| Output Noise Voltage V_{out1} (V_{in} = 4.5 V, f = 20 Hz - 80 kHz, I_{out1} = 20 mA) V_{out2} (V_{in} = 4.5 V, f = 20 Hz - 80 kHz, I_{out2} = 40 mA) | V _n | - - | 80 50 | - - | μV_{rms} |
| V _{in} Detect | | | | | |
| Detecting Voltage L (V _{in} = H to L) | V_{SLin} | 6.72 | 7.0 | 7.28 | V |
| Detecting Voltage H (V _{in} = L to H) | V_{SHin} | _ | 7.35 | - | V |
| Hysteresis Voltage (V _{in} = H to L to H) | ΔV_{Sin} | 140 | 350 | 560 | mV |
| V_{SLin} Temperature Coefficient (T _J = -30°C to +85°C) | V _{Slin} T _C | _ | 100 | - | ppm/°C |
| Low-Level Output Voltage (V_{in} = 6.0 V, Vt1 = 5.0 V, Rt1 = 10 k Ω) (Note 5) Threshold Operating Voltage (V_{OPLin} = Vt1 = 1.0 V) | V _{OLin1} V _{OLin2} | 1 1 | 100 - | 200 0.4 | mV V |
| V _{out} Detect | | | | | |
| Detecting Voltage L (V _{in} = H to L) | V_{SLout} | 2.78 | 2.9 | 3.020 | V |
| Detecting Voltage H (V _{in} = L to H) | V_{SHout} | _ | 2.95 | - | V |
| Hysteresis Voltage (V _{in} = H to L to H) | Δ V _{Sout} | 25 | 50 | 100 | mV |
| V_{SLin} Temperature Coefficient (T _J = -30°C to +85°C) | V _{SLin} T _C | - | 100 | - | ppm/°C |
| Low-Level Output Voltage (V _{out1} = 2.6 V) Threshold Operating Voltage (V _{OPLout} = 0.85 V) | V _{OLout1} V _{OLout2} | - | 100 - | 200 0.4 | mV V |
| Reset Delay Time (C _D = 10 nF) | t _{PLH} | 5 | 10 | 15 | ms |
| "I " Transmission Dalay Time (C- 10 nE) | + | | 20 | 00 | |

This device series contains ESD protection and exceeds the following tests:
 Human Body Model 2000 V per MIL-STD-883, Method 3015
 Machine Model Method 200 V.

- 3. The maximum package power dissipation is: $P_D = \frac{T_J(max) T_A}{R_{O,LA}}$
- 4. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

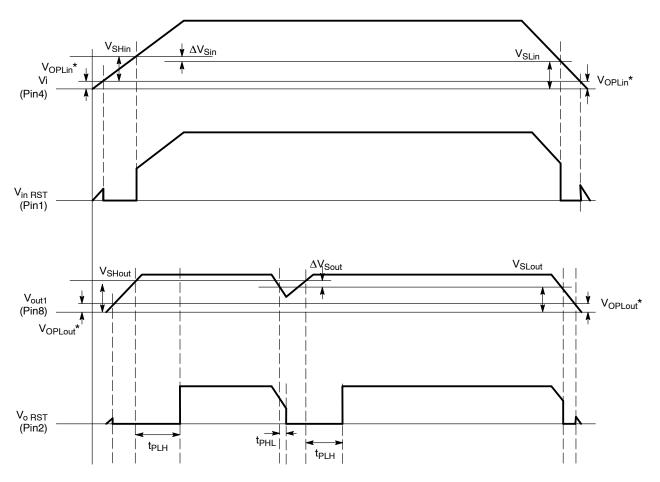
 5. Refer to Figure 3.

 6. Guaranteed by design.

"L" Transmission Delay Time ($C_D = 10 \text{ nF}$)

90

μs



^{*;} V_{OPLin} shows theoretical on this chart. V_{OPLin} spec. must be specified on Pin 1 voltage (0.4 V)

Figure 2. Dual Regulator Timing

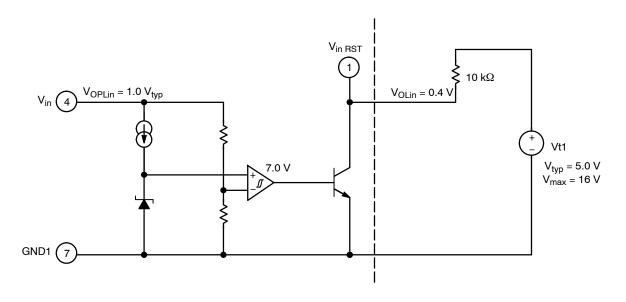


Figure 3. Threshold Operating Voltage V_{OPLin} Under Condition V_{OLin} = 0.4 V

^{*;} V_{OPLout} shows theoretical on this chart. V_{OPLout} spec. must be specified on Pin 2 voltage (0.4 V)

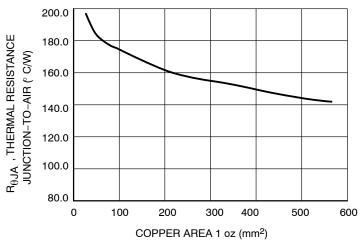


Figure 4. SOP-8 Thermal Resistance versus P.C.B. Copper Area

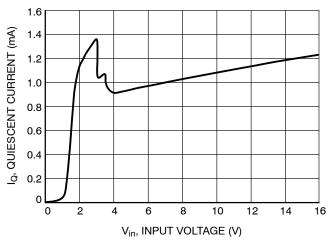


Figure 5. Quiescent Current versus Input Voltage

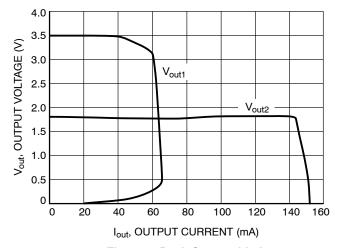


Figure 6. Peak Current Limit

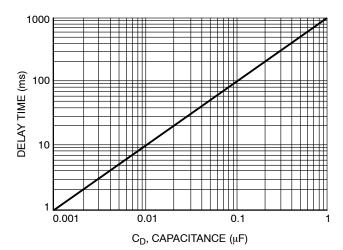


Figure 7. Delay Time versus Capacitance

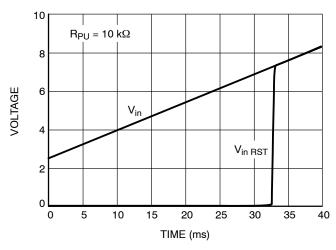


Figure 8. V_{in} and $V_{in\,RST}$ versus Time

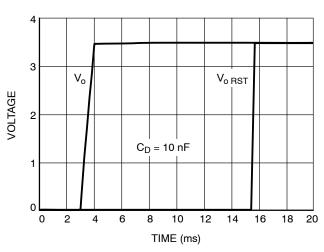


Figure 9. $\ensuremath{V_{o}}$ and $\ensuremath{V_{o}}$ RST versus Time

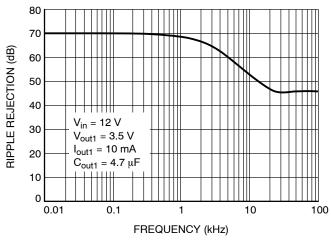


Figure 10. Vout1 Ripple Rejection

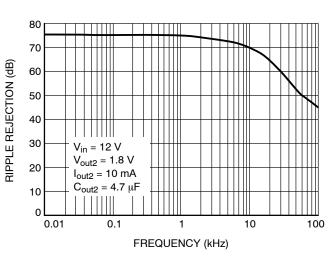


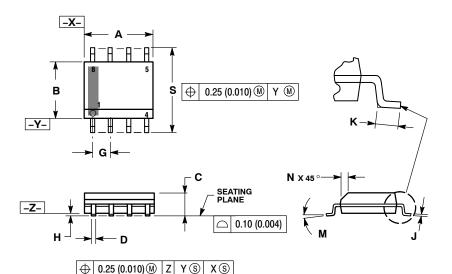
Figure 11. V_{out2} Ripple Rejection





SOIC-8 NB CASE 751-07 **ISSUE AK**

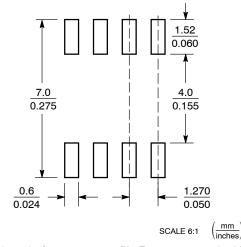
DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

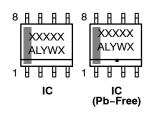
| | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 4.80 | 5.00 | 0.189 | 0.197 |
| В | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| Н | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| М | 0 ° | 8 ° | 0 ° | 8 ° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

SOLDERING FOOTPRINT*



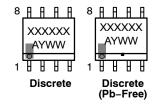
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week W

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

| DOCUMENT NUMBER: | 98ASB42564B | Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | | |
|------------------|-------------|---|-------------|--|
| DESCRIPTION: | SOIC-8 NB | | PAGE 1 OF 2 | |

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

| | | | D/ (I E TO I ED E |
|--|---|---|--|
| STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER | STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1 STYLE 6: | STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 STYLE 7: | |
| PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE | PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE | STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd | PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1 |
| STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON | STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND | STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1 | STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN |
| STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN | STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN | 7. DHAIN 1 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON | STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1 |
| STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC | STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE | STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 | STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN |
| STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6 | STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND | STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT | STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE |
| STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT | STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC | STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN | STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN |
| STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1 | STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1 | | |

| DOCUMENT NUMBER: | 98ASB42564B | Printed versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | | |
|------------------|-------------|--|-------------|--|
| DESCRIPTION: | SOIC-8 NB | | PAGE 2 OF 2 | |

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales